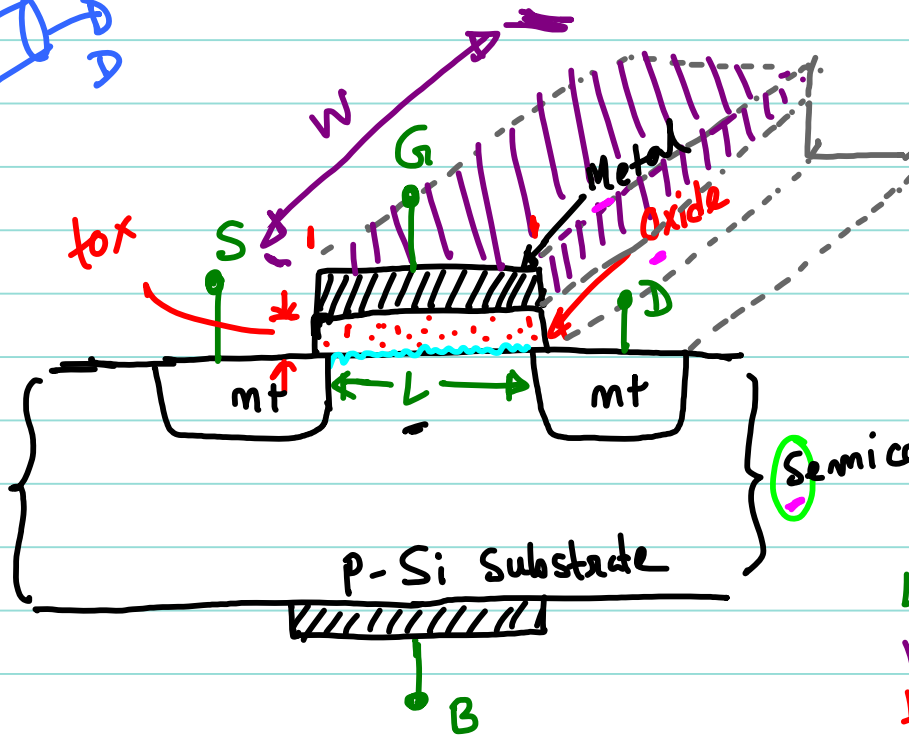


Lec-21

→ MOSFET ⇒ Metal Oxide Semiconductor field Effect Transistor



Terminals

- G → gate
- S → source
- D → Drain
- B → Body

L → Channel length

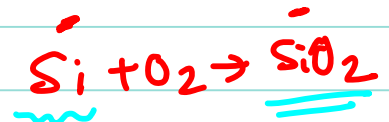
W → Width

tox → oxide thickness

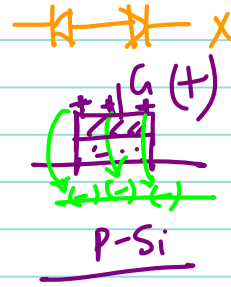
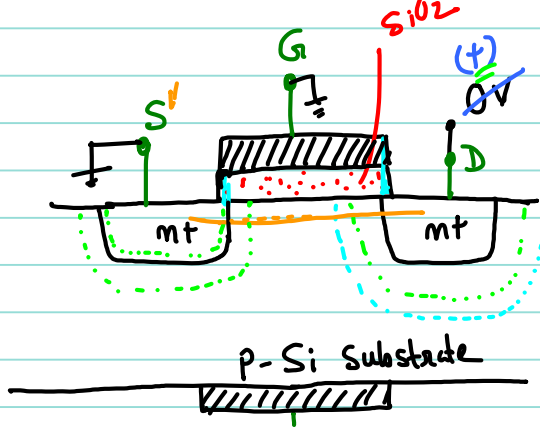


SiO₂

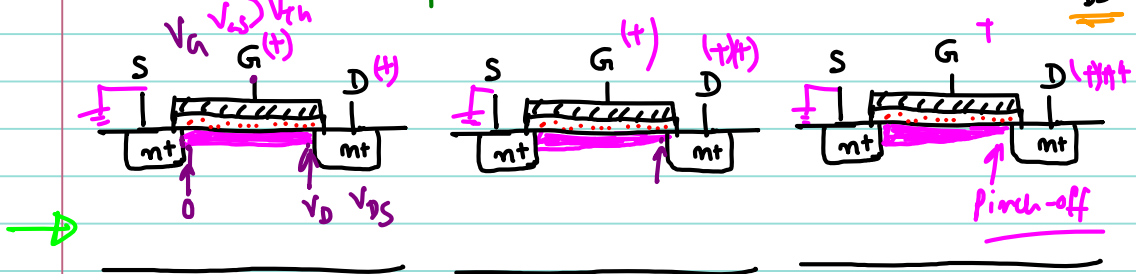
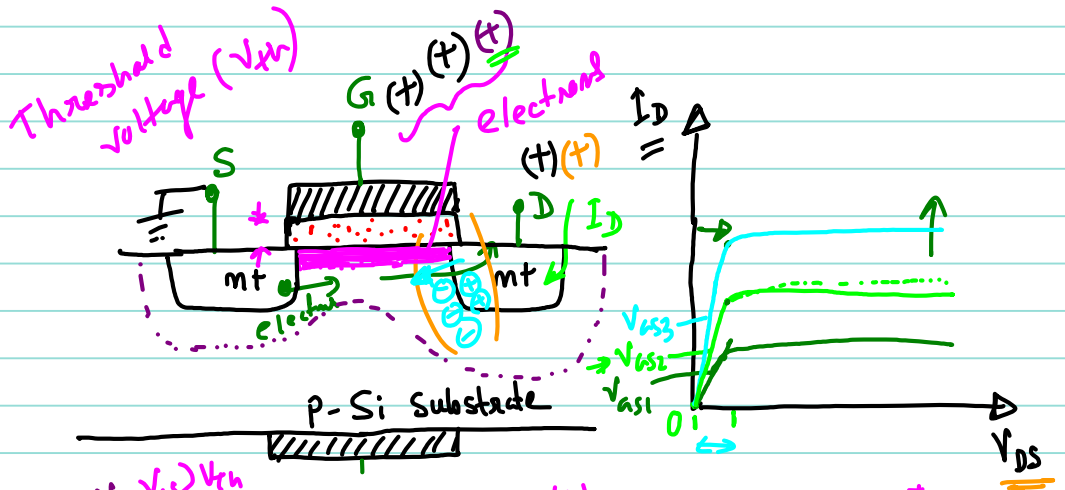
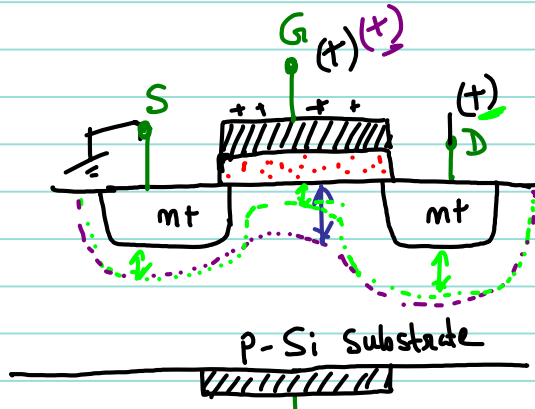
MOSFET → IGFET [Insulated Gate FET]



Operation of MOSFET:



$\uparrow \ominus \ominus \ominus$



$$V_G = V_{GS} \quad \therefore V_S = 0$$

